L Number	Hits	Search Text	DB	Time stamp
1	196866	mold	USPAT;	2004/03/18 16:02
1	190800	Hold	US-PGPUB	2004/05/10 10:02
ا ، ا	205490	incort	USPAT;	2004/03/18 15:55
2	295480	insert	,	2004/03/16 13.33
	400004	totoatos	US-PGPUB	2004/02/19 15:55
3	422304	injection	USPAT;	2004/03/18 15:55
			US-PGPUB	2004/02/10 16 01
4	138097	wafer	USPAT;	2004/03/18 16:01
_		ļ.,.	US-PGPUB	2004/02/10 15 55
5	83359	masking	USPAT;	2004/03/18 15:55
	****		US-PGPUB	2004/02/10 15 55
6	233471	etch\$3	USPAT;	2004/03/18 15:55
_			US-PGPUB	
7	273061	mask\$3	USPAT;	2004/03/18 15:55
			US-PGPUB	
8	523095	mold\$3	USPAT;	2004/03/18 15:56
			US-PGPUB	
9	4017	wafer and etch\$3 and mask\$3 and mold\$3	USPAT;	2004/03/18 16:03
			US-PGPUB	
10	867	(wafer and etch\$3 and mask\$3 and mold\$3 ) and 438/\$.ccls.	USPAT;	2004/03/18 16:48
			US-PGPUB	
11	622457	wafer substrate	USPAT;	2004/03/18 16:01
			US-PGPUB	
12	100827	etch\$3 with (wafer substrate)	USPAT;	2004/03/18 16:02
		, ·	US-PGPUB	
13	236451	mold	USPAT;	2004/03/18 16:02
			US-PGPUB	
14	5283	mask\$3 and mold\$3 and (etch\$3 with (wafer substrate))	USPAT;	2004/03/18 16:52
			US-PGPUB	
15	867	((wafer and etch\$3 and mask\$3 and mold\$3 ) and 438/\$.ccls.) and	USPAT;	2004/03/18 16:52
		438/\$.ccls.	US-PGPUB	
16	1506398	metal conductive	USPAT;	2004/03/18 16:04
			US-PGPUB	
17	76933	mold\$3 with (metal conductive)	USPAT;	2004/03/18 16:05
		(,	US-PGPUB	
18	209	(((wafer and etch\$3 and mask\$3 and mold\$3 ) and 438/\$.ccls.) and	USPAT;	2004/03/18 16:47
		438/\$.ccls.) and (mold\$3 with (metal conductive))	US-PGPUB	
19	548771	carrier	USPAT;	2004/03/18 16:06
''	0.0.71		US-PGPUB	
20	64	(((((wafer and etch\$3 and mask\$3 and mold\$3 ) and 438/\$.ccls.) and	USPAT;	2004/03/18 16:07
	• • • • • • • • • • • • • • • • • • • •	438/\$.ccls.) and (mold\$3 with (metal conductive))) and carrier	US-PGPUB	
21	145	((((wafer and etch\$3 and mask\$3 and mold\$3 ) and 438/\$.ccls.) and	USPAT;	2004/03/18 16:30
	1.15	438/\$.ccls.) and (mold\$3 with (metal conductive))) not (((((wafer and etch\$3	US-PGPUB	
		and mask\$3 and mold\$3 ) and 438/\$.ccls.) and 438/\$.ccls.) and (mold\$3		
		with (metal conductive))) and carrier)		
22	1256	(mask\$3 and mold\$3 and (etch\$3 with (wafer substrate))) and (mold\$3 with	USPAT;	2004/03/18 16:52
	1250	(metal conductive))	US-PGPUB	
23	230	((mask\$3 and mold\$3 and (etch\$3 with (wafer substrate)) ) and (mold\$3	USPAT;	2004/03/18 17:00
==	200	with (metal conductive))) and 438/\$.ccls.	US-PGPUB	
24	97	(((mask\$3 and mold\$3 and (etch\$3 with (wafer substrate))) and (mold\$3	USPAT;	2004/03/18 16:53
	,,	with (metal conductive))) and 438/\$.ccls.) not ((((wafer and etch\$3 and	US-PGPUB	
		mask\$3 and mold\$3 ) and 438/\$.ccls.) and 438/\$.ccls.) and (mold\$3 with	33 1 31 35	
		(metal conductive)))		
25	111	((mask\$3 and mold\$3 and (etch\$3 with (wafer substrate))) and (mold\$3	USPAT;	2004/03/18 17:00
23	111	with (metal conductive))) and 216/\$.ccls.	US-PGPUB	
L		with (metal conductive))) and 210/0.cels.	1 22 1 01 01	1